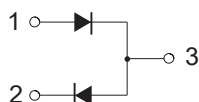
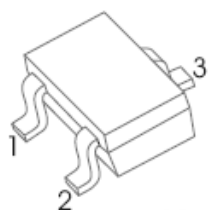


Features

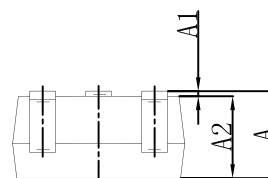
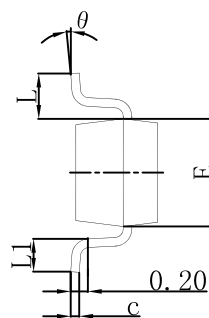
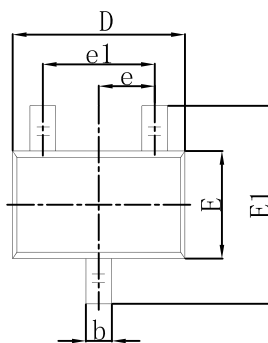
- For high-speed switching applications
- Connected in series

SOT-323



Marking :A7

SOT-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	75	V
Forward Current	I_F	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{STG}	-55~+150	°C

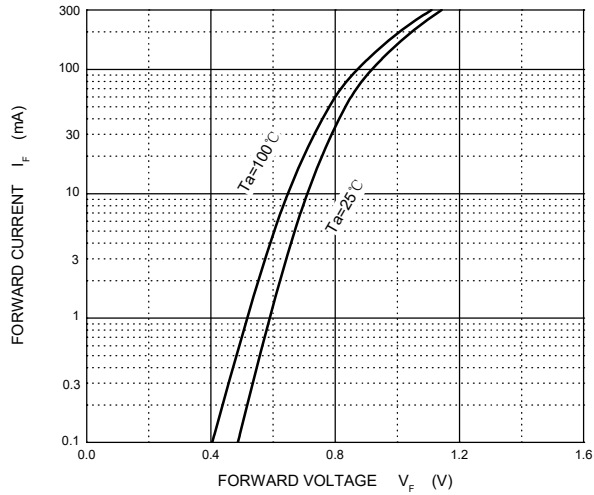
BAV99W

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

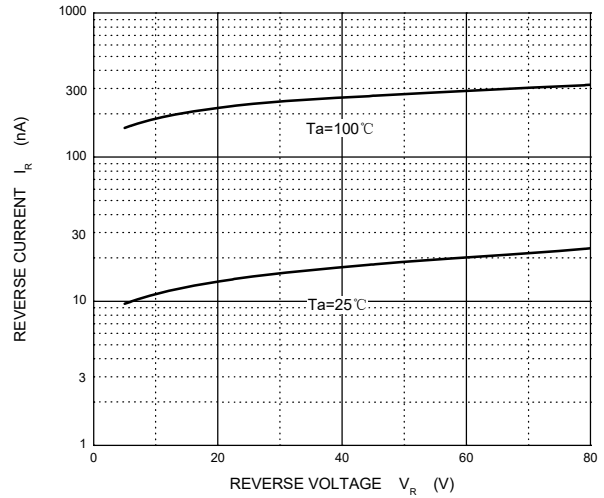
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	75		V
Reverse voltage leakage current	I_{R1}	$V_R = 75V$		2.5	μA
	I_{R2}	$V_R = 25V$		25	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R = 0$ $f = 1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	ns

RATING AND CHARACTERISTIC CURVES (BAV99W)

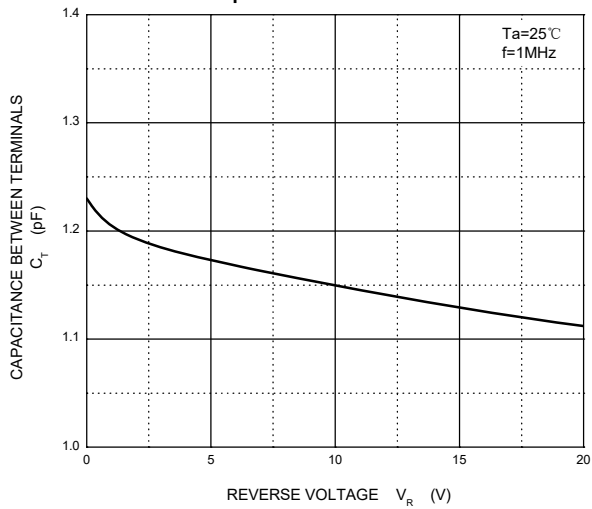
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

